KL3G-1010-SiO2/Si Product Datasheet

KL3G-1010-SiO2/Si is a single 10mmx10mm trilayer of CVD graphene film, on silicon. All three layers of graphene were grown on copper foil, and transferred individually by wet film transfer to the silicon substrate.

Graphene Film

Growth Method	CVD synthesis
Transfer Method	Clean transfer method
Quality Control	Optical Microscopy & Raman checked
Appearance (Color)	Transparent
Transparency	>97%
Appearance (Form)	Film
Coverage	>95%
Number of graphene layers	3
Thickness (theoretical)	1.04 nm
Field Effect Mobility on SiO_2/Si	2,000 $cm^2/V{\cdot}s$
Hall Effect Mobility on SiO_2/Si	4,000 $cm^2/V{\cdot}s$
Sheet Resistance on SiO_2/Si (Van der Pauw)	126±6 Ohms/sq. (1cm x 1cm)
Grain size	Up to 10 µm

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Substrate

	SiO_2/Si
Type/Dopant	P/Bor
Orientation	<100>
Growth Method	CZ
Resistivity	<0.005 ohm cm
Thickness	525 +/- 20 µm
Font Surface	Polished
Back Surface	Etched
Flats	2 SEMI

Optical Microscopy